

ABSTRACT OF THE DISCLOSURE

When a SiC substrate is heated up to around 1800 °C, sublimation of SiC occurs from the SiC substrate. Moreover, temperature of the front surface of the SiC substrate is lower than that of the back surface of the SiC substrate. Therefore, sublimation gas sublimed from a back-surface vicinity of the substrate, where temperature is high, moves to a front-surface vicinity of the substrate, where temperature is low, through the hollow micro-pipe defect. Epitaxial growth proceeds on the front surface of the substrate while the sublimation gas is recrystallized at the front-surface vicinity of the substrate, so that the micro-pipe defect is occluded.